

INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small> <div style="border: 1px solid black; border-radius: 50%; padding: 10px; width: fit-content; margin: auto;"> DEC 07 2005 PATENT & TRADEMARK OFFICE </div>				Docket Number (Optional) FIS920030189US1		Application Number 10/707,018		
				Applicant(s) Bruce B. Doris, et al.				
				Filing Date 11/14/03		Group Art Unit 2812		
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
WLL		6,281,559	8/28/01	Yu et al.				
WLC		6,787,827	9/7/04	Inumiya et al.				
U.S. PATENT APPLICATION PUBLICATIONS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
WLL		International Search Report and Written Opinion, International Application No. PCT/US2004/037434, International Filing Date 09 November 2004						
EXAMINER		<i>[Signature]</i>			DATE CONSIDERED 11/17/2006			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

FORM PTO-1449 (Modified) **FEB 2 2005**

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.
FIS920030189US1

SERIAL NO.
10/707,018

APPLICANT:
Doris, et al.

FILING DATE:
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REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
WLL	6,228,694 B1	5/8/2001	Doyle et al.			
WLL	6,406,973 B1	6/18/2002	Lee			
WLL	6,281,532 B1	8/28/2001	Doyle et al.			
WLL	5,683,934	11/4/97	Candelaria			
WLL	6,368,931 B1	4/9/2002	Kuhn, et al.			
WLL	5,310,446	5/10/94	Konishi et al.			
WLL	4,853,076	8/1/89	Tsaur et al.			
WLL	US 2002/0090791 A1	7/11/2002	Doyle et al.			
WLL	US 2002/0074598 A1	6/20/2002	Doyle et al.			
WLL	6,509,618 B2	1/21/2003	Jan et al.			
WLL	6,476,462 B2	11/5/2002	Shimizu et al.			
WLL	6,362,082 B1	3/26/2002	Doyle et al.			
WLL	6,228,694 B1	5/8/2001	Doyle et al.			
WLL	5,565,697	10/15/96	Asakawa et al.			
WLL	US 2003/0040158 A1	2/27/2003	Saitoh			
WLL	US 2002/0086472 A1	7/4/2002	Roberds et al.			
WLL	6,521,964 B1	2/18/2003	Jan et al.			
WLL	6,506,652	01/14/03	Jan, et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER *WLL* *Trish* **DATE CONSIDERED** *11/17/2006*

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
WLL	5,081,513	1/14/1992	Jackson, et al.			
WLL	3,602,841	8/31/1971	McGroddy			
WLL	6,531,740	3/11/2003	Bosco, et al.			
WLL	6,531,369	3/11/2003	Ozkan, et al.			
WLL	6,501,121	12/31/2002	Yu, et al.			
WLL	6,498,358	12/24/2002	Lach, et al.			
WLL	6,493,497	12/10/2002	Ramdani, et al.			
WLL	6,403,975	6/11/2002	Brunner, et al.			
WLL	6,361,885	3/26/2002	Chou			
WLL	6,255,169	7/3/2001	Li, et al.			
WLL	6,246,095	6/12/2001	Brady, et al.			
WLL	6,165,383	12/26/2000	Chou			
WLL	6,133,071	10/17/2000	Nagai			
WLL	6,046,464	4/4/2000	Schetzina			
WLL	6,025,280	2/15/2000	Brady, et al.			

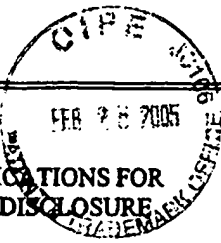
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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
WLL	5,940,736	8/17/1999	Brady, et al.			
WLL	5,880,040	3/9/1999	Sun, et al.			
WLL	5,861,651	1/19/1999	Brasen, et al.			
WLL	5,679,965	10/21/1997	Schetzina			
WLL	5,670,798	9/23/1997	Schetzina			
WLL	5,561,302	10/1/1996	Candelaria			
WLL	5,471,948	12/5/1995	Burroughes, et al.			
WLL	5,459,346	10/17/1995	Asakawa, et al.			
WLL	5,391,510	2/21/1995	Hsu, et al.			
WLL	5,371,399	12/6/1994	Burroughes, et al.			
WLL	5,108,843	4/28/1992	Ohtaka, et al.			
WLL	5,060,030	10/22/1991	Hoke			
WLL	4,958,213	9/18/1990	Eklund, et al.			
WLL	4,665,415	5/12/1987	Esaki, et al.			
WLL	6,635,506	10/21/2003	Volant et al.			

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
WLL	5,989,978	11/23/1999	Peidous			
WLL	6,284,626	9/4/2001	Kim			
WLL	6,274,444	8/14/2001	Wang			
WLL	6,261,964	7/17/2001	Wu, et al.			
WLL	6,221,735	4/24/2001	Manley, et al.			
WLL	6,117,722	9/12/2000	Wuu, et al.			
WLL	6,107,143	8/22/2000	Park, et al.			
WLL	6,090,684	7/18/2000	Ishitsuka, et al.			
WLL	6,066,545	5/23/2000	Doshi, et al.			
WLL	6,008,126	12/28/1999	Leedy			
WLL	5,946,559	8/31/1999	Leedy			
WLL	5,840,593	11/24/1998	Leedy			
WLL	5,592,018	1/7/1997	Leedy			
WLL	5,592,007	1/7/1997	Leedy			
WLL	5,571,741	11/5/1996	Leedy			

FOREIGN PATENT DOCUMENTS

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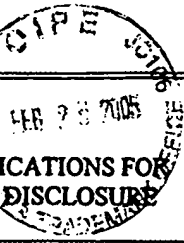
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WLL	5,557,122	9/17/1996	Shrivastava, et al.			
WLL	5,354,695	10/11/1994	Leedy			
WLL	5,134,085	7/28/1992	Gilgen, et al.			
WLL	5,006,913	4/9/1991	Sugahara, et al.			
WLL	4,952,524	8/28/1990	Lee, et al.			
WLL	4,855,245	8/8/1989	Neppl, et al.			
WLL	2002/0086497	07-04-2002	Kwok			
WLL	5,960,297	09-28-1999	Saki			
WLL	6,403,486	06-11-2002	Lou			
WLL	6,284,623	09-04-2001	Zhang et al.			
WLL	2003/0032261	02-13-2003	Yeh et al.			
WLL	2003/0057184 ✓	03-27-2003	Yu et al.			
WLL	6,265,317	07-24-2001	Chiu et al.			
WLL	2003/0067035 ✓	04-10-2003	Tews et al.			
WLL	6,461,936	10-08-2002	von Ehrenwall			
WLL	6,319,794	11-20-2001	Akatsu et al.			
WLL	2001/0009784	07-26-2001	Ma et al.			
WLL	6,621,392	09-16-2003	Volant et al.			

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Group Art Unit

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Supplemental FORM PTO-1449 (Modified)	ATTY. DOCKET NO. FIS920030189US1	SERIAL NO. 10/707,018
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					YES NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

WLL	Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
WLL	Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
WLL	Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
WLL	F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
WLL	Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
WLL	A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
WLL	K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

EXAMINER <i>WLL</i>	DATE CONSIDERED 1/17/2006
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							YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

WCL		G. Zhang, J. Cressler, G. Niu, A. Joseph, "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors". IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.
WCL		H.S. Momose, Y. Niitsu, H. Iwai, K. Maeguchi, "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures". Paper 6.2, pp. 140-143.

EXAMINER	<i>WCL</i>	DATE CONSIDERED	1/17/2006
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							YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

WLL	C.J. Huang, C.J. Sun, T.A. Grotjohn, D.K. Reinhard, "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors". IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.
WLL	S.R. Sheng, S.P. McAllister, J.P. McCaffrey, S. Kovacic, "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing". Pp. 14-15.

EXAMINER

Walter L. Reinhard

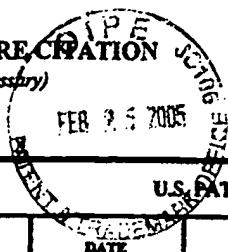
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1/17/2000

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OTHER DOCUMENTS

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WLL	Z. Yang, F. Gaurin, E. Hostetter, G. Freeman, "Avalanche Current Induced Hot Carrier Degradation in 200GHz SiGe Heterojunction Bipolar Transistors". Pp. 1-5.
WLL	H. Li, H.M. Rein, T. Suttrop, "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems". 2003 IEEE CAs Digest, pp. 263-266.

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WLL		H. Wurzer, R. Mahnkopf, H. Klose, "Annealing of Degraded n-p-n Transistors- Mechanisms and Modeling". IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-538.
WLL		B. Doyle, G.J. Dunn, "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFET's". IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.

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H.S. Momose, H. Iwai, "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS". IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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